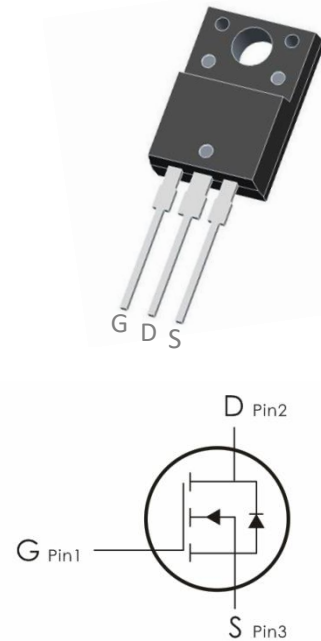


Description:

This N-Channel MOSFET uses advanced Planar technology and design to provide excellent $R_{DS(on)}$ with low gate charge. It can be used in a wide variety of applications.

Features:

- 1) $V_{DS}=200V, I_D=9A, R_{DS(ON)} < 400m\ \Omega @ V_{GS}=10V$ (Typ: $330m\ \Omega$)
- 2) Low gate charge.
- 3) Green device available.
- 4) Advanced high cell density Planar technology for ultra low $R_{DS(ON)}$.
- 5) Excellent package for good heat dissipation.



Package Marking and Ordering Information:

Part NO.	Marking	Package	Packing
FJ09NG-H	J09N-H	TO- 220F	50 pcs/Tube

Absolute Maximum Ratings: ($T_C=25^\circ C$ unless otherwise noted)

Symbol	Parameter	Ratings	Units
V_{DS}	Drain-Source Voltage	200	V
V_{GS}	Gate-Source Voltage	± 30	V
I_D	Continuous Drain Current ¹	9	A
	Continuous Drain Current- $T_C=100^\circ C$ ¹	6.3	
I_{DM}	Pulsed Drain Current ²	36	
P_D	Power Dissipation	13	W
E_{AS}	Single pulse avalanche energy ³	61	mJ
T_J, T_{STG}	Operating and Storage Junction Temperature Range	-55-+150	$^\circ C$

Thermal Characteristics:

Symbol	Parameter	Max	Units
$R_{\theta JC}$	Thermal Resistance, Junction to Case	9	$^\circ C/W$
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	80	$^\circ C/W$

Electrical Characteristics: ($T_C=25^{\circ}\text{C}$ unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Units
Off Characteristics						
BV_{DSS}	Drain-Source Breakdown Voltage	$V_{GS}=0V, I_D=250\ \mu\text{A}$	80	---	---	V
I_{DSS}	Zero Gate Voltage Drain Current	$V_{GS}=0V, V_{DS}=64V$	---	---	1	μA
I_{GSS}	Gate-Source Leakage Current	$V_{GS}=\pm 30V, V_{DS}=0A$	---	---	± 100	nA
On Characteristics						
$V_{GS(th)}$	Gate-Source Threshold Voltage	$V_{GS}=V_{DS}, I_D=250\ \mu\text{A}$	2	3.27	4	V
$R_{DS(ON)}$	Drain-Source On Resistance ⁴	$V_{GS}=10V, I_D=4.5A$	---	330	400	$\text{m}\Omega$
Dynamic Characteristics						
C_{iss}	Input Capacitance	$V_{DS}=25V, V_{GS}=0V, f=1\text{MHz}$	---	550	---	pF
C_{oss}	Output Capacitance		---	90.3	--	
C_{rss}	Reverse Transfer Capacitance		---	5.3	---	
Switching Characteristics						
$t_{d(on)}$	Turn-On Delay Time	$V_{DS}=100V, I_D=9A,$ $R_{ENG}=25\ \Omega, V_{GS}=10V$	---	9	---	ns
t_r	Rise Time		---	3.4	---	ns
$t_{d(off)}$	Turn-Off Delay Time		---	29.4	---	ns
t_f	Fall Time		---	3.5	---	ns
Q_g	Total Gate Charge		$V_{GS}=10V, V_{DS}=160V,$ $I_D=9A$	---	22	---
Q_{gs}	Gate-Source Charge	---		5.6	---	nC
Q_{gd}	Gate-Drain "Miller" Charge	---		4	---	nC
Drain-Source Diode Characteristics						
V_{SD}	Diode Forward Voltage	$V_{GS}=0V, I_{SD}=9A$	---	---	1.2	V
I_S	Continuous Drain Current	$V_D=V_G=0V$	---	---	7.5	A
I_{SM}	Pulsed Drain Current		---	---	30	A
T_{rr}	Reverse Recovery Time	$I_F=9A, T_J=25^{\circ}\text{C}$	---	103	---	ns
Q_{rr}	Reverse Recovery Charge	$di/dt=100A/\mu\text{s}$	---	411	---	nC

Notes:

1. Computed continuous current assumes the condition of $T_{j,Max}$ while the actual continuous current depends on the thermal & electro-mechanical application board design
2. Repetitive Rating: Pulse Width Limited by Maximum Junction Temperature
3. EAS condition : $T_J=25^{\circ}C, V_{DD}=100V, V_G=10V, L=10mH$
4. Pulse Test: Pulse Width $\leq 300\mu s$, Duty Cycle $\leq 0.5\%$

Test Circuit

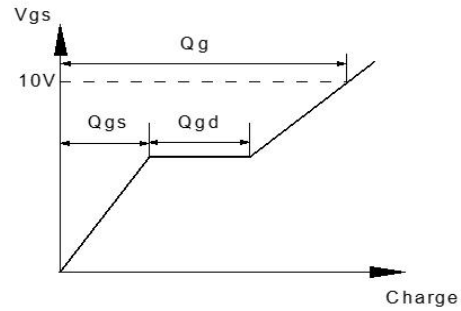
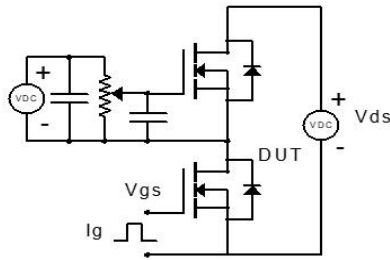


Figure 1: Gate Charge Test Circuit & Waveform

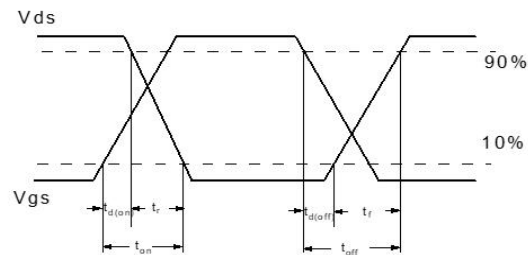
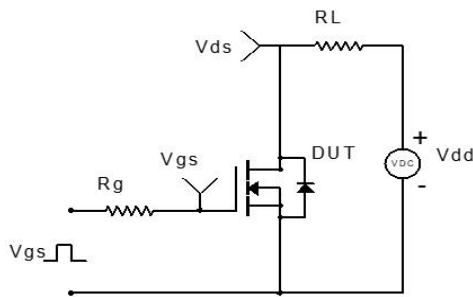


Figure 2: Resistive Switching Test Circuit & Waveform

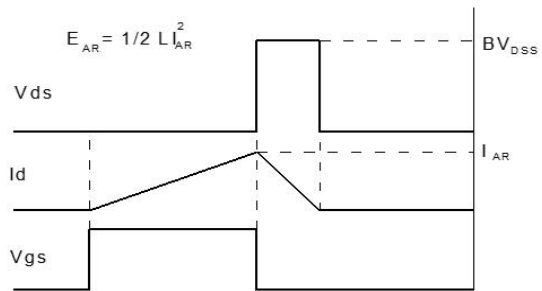
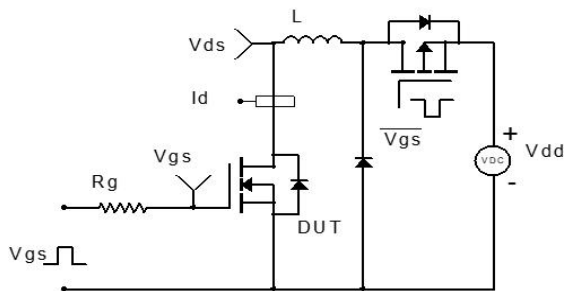


Figure 3: Unclamped Inductive Switching Test Circuit & Waveform

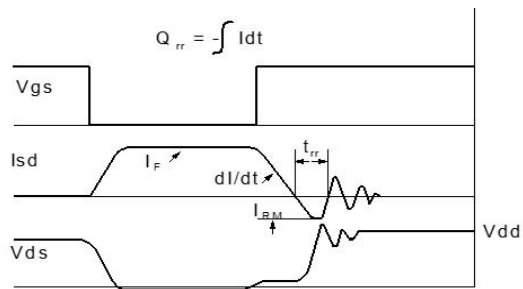
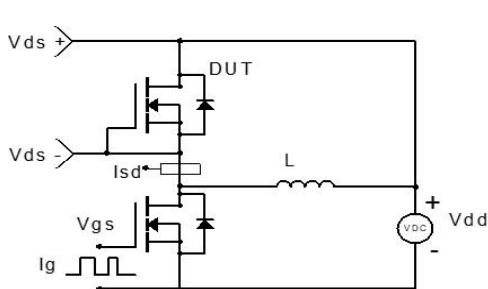
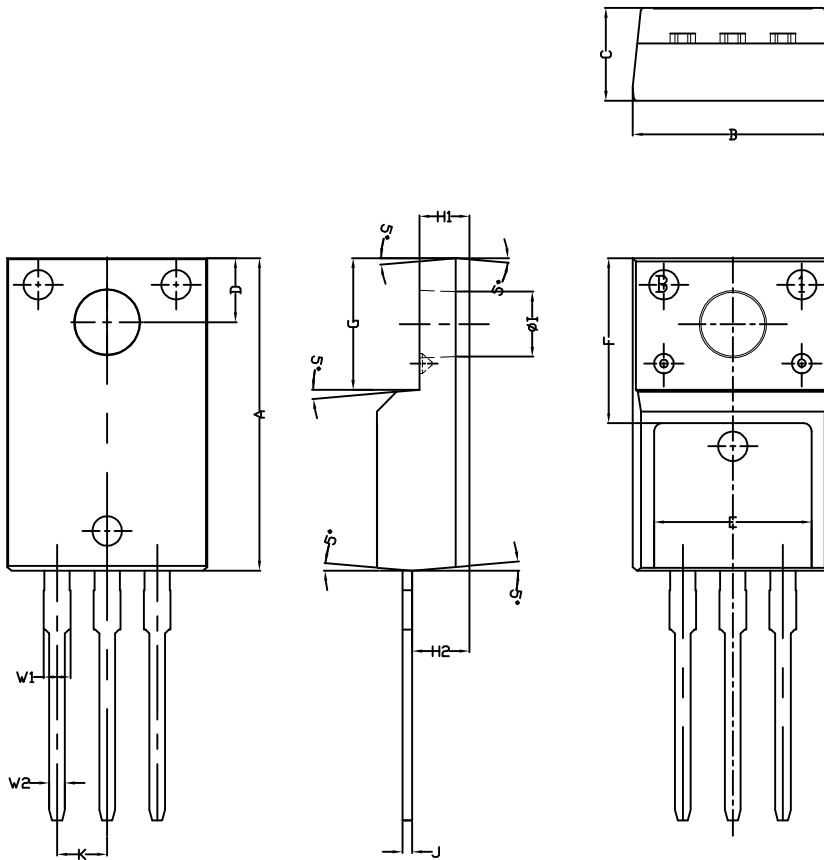


Figure 4: Diode Recovery Test Circuit & Waveform

TO-220F Package Information:


Symbol	MM			Inch		
	Min	Mim	Max	Min	Mim	Max
A	15.67	15.87	16.07	0.6169	0.6248	0.6328
B	9.86	10.16	10.46	0.3882	0.4000	0.4118
C	4.50	4.70	4.90	0.1772	0.1850	0.1929
D	3.15	3.35	3.55	0.1240	0.1319	0.1398
E	7.80	8.00	8.20	0.3071	0.3150	0.3228
F	8.18	8.38	8.58	0.3220	0.3299	0.3378
H1	2.34	2.54	2.84	0.0921	0.1000	0.1118
H2	2.40	2.90	3.40	0.0945	0.1141	0.1339
I	3.10	3.30	3.50	0.1220	0.1299	0.1378
W1	1.08	1.28	1.48	0.0425	0.0504	0.0583
W2	0.70	0.80	0.90	0.0276	0.0315	0.0354
K	2.44	2.54	2.64	0.0961	0.1000	0.1039
G	6.48	6.68	6.88	0.2551	0.2630	0.2709
J	0.45	0.50	0.6	0.0177	0.0197	0.0236

Marking Information:

①. Doingter LOGO

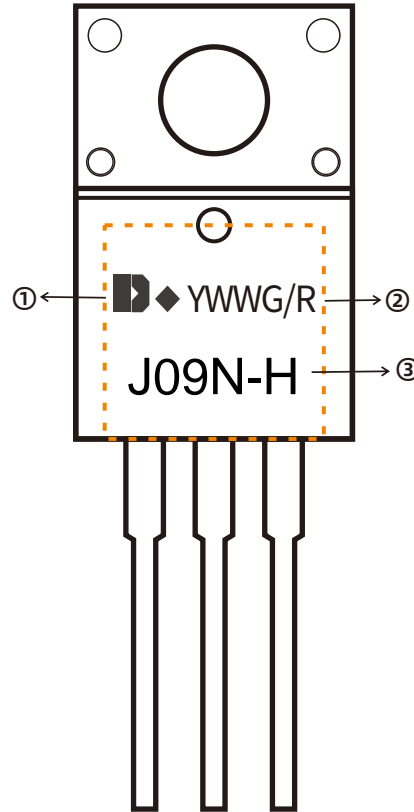
②. Date Code(YWWG / R)

Y : Year Code , last digit of the year

WW : Week Code(01-53)

G/R : G(Green) /R(Lead Free)

③. Part NO.



Previous Version

Version	Date	Subjects (major changes since last revision)
1.0	2025-09-17	Release of final version

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